NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into six groups, D, E, F, G, H and I, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25° C)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	30	V
Collector Emitter Voltage	V _{CEO}	V _{CEO} 20	
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	Ι _c	25	mA
Power Dissipation	P _{tot}	400	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-65 to +150	°C

G S P FORM A IS AVAILABLE

SEMTECH ELECTRONICS LTD. (Subsidiary of Semtech International Holdings Limited, a company

listed on the Hong Kong Stock Exchange, Stock Code: 724)





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ST 9016

Characteristics at T_{amb} =25 ^oC

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =5V, I _C =1mA					
Current Gain Group D	h_{FE}	28	-	45	-
E	h _{FE}	39	-	60	-
F	h _{FE}	54	-	80	-
G	h_{FE}	72	-	108	-
н	h_{FE}	97	-	146	-
1	h_{FE}	132	-	198	-
Collector Base Breakdown Voltage					
at I _C =100μA	V _{(BR)CBO}	30	-	-	V
Collector Emitter Breakdown Voltage					
at I _c =1mA	V _{(BR)CEO}	20	-	-	V
Emitter Base Breakdown Voltage					
at I _E =100μA	$V_{(BR)EBO}$	4	-	-	V
Collector Cutoff Current					
at V _{CB} =30V	I _{CBO}	-	-	100	nA
Emitter Cutoff Current					
at V _{EB} =3V	I _{EBO}	-	-	100	nA
Collector Emitter Saturation Voltage					
at I _C =10mA, I _B =1mA	$V_{\text{CE(sat)}}$	-	0.1	0.3	V
Base Emitter on Voltage					
at V _{CE} =5V, I _C =1mA	$V_{\text{BE(on)}}$	-	0.72	-	V
Collector Base Capacitance					
at V _{CB} =10V, f=1MHz	C _{CBO}	-	1.2	1.6	pF
Gain Bandwidth Product					
at V _{CE} =5V, I _C =1mA	f _T	400	620	-	MHz

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